

XPT IGBT

Single IGBT

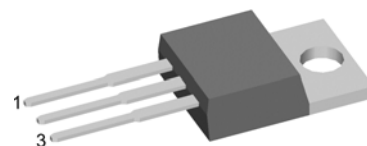
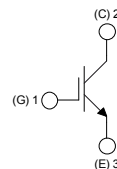
$$I_{C25} = 33 \text{ A}$$

$$V_{CES} = 1200 \text{ V}$$

$$V_{CE(sat)typ} = 1.8 \text{ V}$$

Part number

IXA20I1200PB



Features / Advantages:

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
 - short circuit rated for 10 μ sec.
 - very low gate charge
 - low EMI
 - square RBSOA @ 3x I_C
- Thin wafer technology combined with the XPT design results in a competitive low $V_{CE(sat)}$

Applications:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies
- Inductive heating, cookers

Package:

- Housing: TO-220
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

IGBT

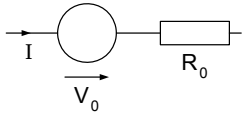
Ratings

Symbol	Definition	Conditions	min.	typ.	max.	Unit
V_{CES}	Collector emitter voltage	$V_{GE} = 0 \text{ V}$ $T_{VJ} = 25^\circ\text{C}$			1200	V
V_{GES}	Maximum DC gate voltage	$T_{VJ} = 25^\circ\text{C}$			± 20	V
I_{C25}	Collector current	$T_C = 25^\circ\text{C}$			33	A
I_{C90}		$T_C = 90^\circ\text{C}$			22	A
P_{tot}	Total power dissipation	$T_{VJ} = 25^\circ\text{C}$			130	W
I_{CES}	Collector emitter leakage current	$V_{CE} = V_{CES}$; $V_{GE} = 0 \text{ V}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$			0.1	mA
				0.1		mA
I_{GES}	Gate emitter leakage current	$V_{CE} = 0 \text{ V}$; $V_{GE} = \pm 20 \text{ V}$			500	nA
$V_{CE(sat)}$	Collector emitter saturation voltage	$I_C = 16 \text{ A}$; $V_{GE} = 15 \text{ V}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		1.8	2.1	V
				2.1		V
$V_{GE(th)}$	Gate emitter threshold voltage	$I_C = 0.6 \text{ mA}$; $V_{GE} = V_{CE}$	5.5	6	6.5	V
Q_{Gon}	Total gate charge	$V_{CE} = 600 \text{ V}$; $V_{GE} = 15 \text{ V}$; $I_C = 15 \text{ A}$		47		nC
$t_{d(on)}$	Turn-on delay time			70		ns
t_r	Current rise time			40		ns
$t_{d(off)}$	Turn-off delay time	Inductive load		250		ns
t_f	Current fall time	$V_{CE} = 600 \text{ V}$; $I_C = 15 \text{ A}$		100		ns
E_{on}	Turn-on energy per pulse	$V_{GE} = \pm 15 \text{ V}$; $R_G = 56 \Omega$ $T_{VJ} = 125^\circ\text{C}$		1.55		mJ
E_{off}	Turn-off energy per pulse			1.7		mJ
RBSOA	Reverse bias safe operation area	$V_{GE} = 15 \text{ V}$; $R_G = 56 \Omega$ $V_{CEK} = 1200 \text{ V}$ $T_{VJ} = 125^\circ\text{C}$			45	A
SCSOA	Short circuit safe operation area					
t_{sc}	Short circuit duration	$V_{CE} = 900 \text{ V}$; $V_{GE} = \pm 15 \text{ V}$ $T_{VJ} = 125^\circ\text{C}$			10	μ s
I_{sc}	Short circuit current	$R_G = 56 \Omega$; non-repetitive			60	A
R_{thJC}	Thermal resistance junction to case				0.95	K/W

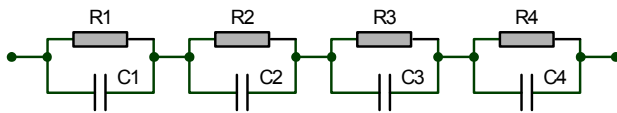
Diode

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	Unit
I_{F25}	Forward current	$T_C = 25^\circ\text{C}$			n/a	A
I_{F90}		$T_C = 90^\circ\text{C}$			n/a	A
V_F	Forward voltage	$I_F = \quad \text{A}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		n/a	n/a	V V
Q_{rr}	Reverse recovery charge	$V_R = 600\text{V};$		n/a		μC
I_{RM}	Maximum reverse recovery current	$di_F/dt = - \quad \text{A}/\mu\text{s};$		n/a		A
t_{rr}	Reverse recovery time	$I_F = \quad \text{A}$ $T_{VJ} = 125^\circ\text{C}$		n/a		ns
$E_{rec(off)}$	Reverse recovery losses at turn-off			n/a		mJ
R_{thJC}	Thermal resistance junction to case				n/a	K/W

Equivalent Circuits for Simulation



Symbol	Definition		Ratings			
			min.	typ.	max.	Unit
V_0	IGBT	$T_{VJ} = 150^\circ\text{C}$			1.1	V
R_0					86	m Ω
V_0	Diode	$T_{VJ} = 150^\circ\text{C}$			n/a	V
R_0					n/a	m Ω



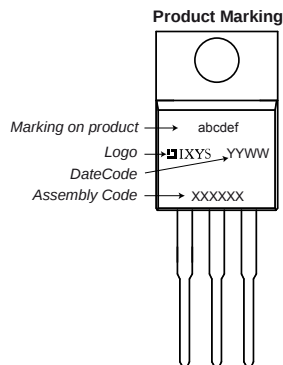
$$Z_{th}(t) = \sum_{i=1}^n \left[R_i \cdot \left(1 - \exp\left(-\frac{t}{\tau_i}\right) \right) \right]$$

$$\tau_i = R_i \cdot C_i$$

	IGBT	Diode
R_1	tbd	n/a
R_2	tbd	n/a
R_3	tbd	n/a
R_4	tbd	n/a
τ_1	tbd	n/a
τ_2	tbd	n/a
τ_3	tbd	n/a
τ_4	tbd	n/a

Package TO-220

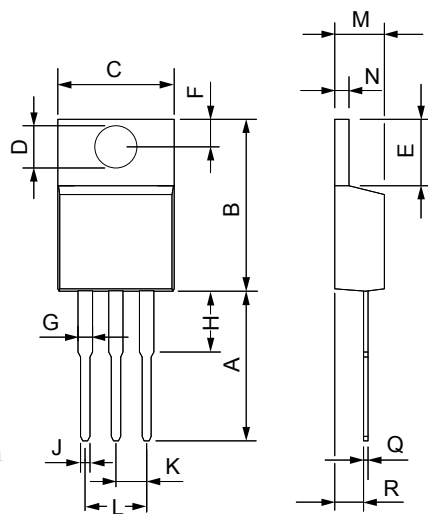
Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	Unit
T_{vj}	Virtual junction temperature		-55		150	°C
T_{stg}	Storage temperature		-55		150	°C
R_{thCH}	Thermal resistance case to heatsink			0.50		K/W
Weight				2		g
M_D	Mounting torque		0.4		0.6	Nm
F_c	Mounting force with clip		20		60	N



Part number

I = IGBT
 X = XPT IGBT
 A = Gen 1 / std
 20 = Current Rating [A]
 I = Single IGBT
 1200 = Reverse Voltage [V]
 PB = TO-220AB (3)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	IXA 20 I 1200 PB	IXA20I1200PB			



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.35	0.56	0.014	0.022
R	2.29	2.79	0.090	0.110

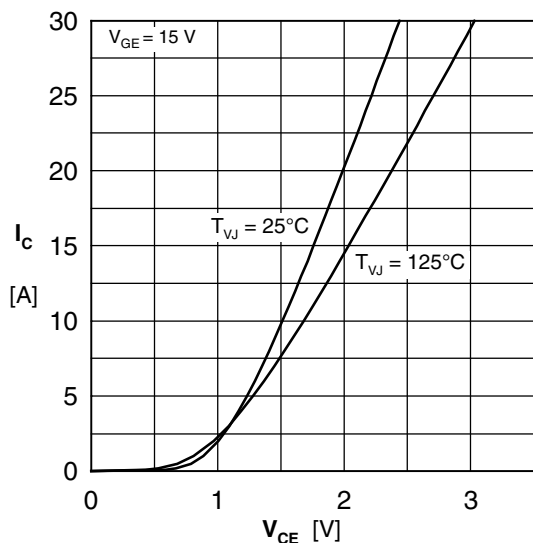


Fig. 1 Typ. output characteristics

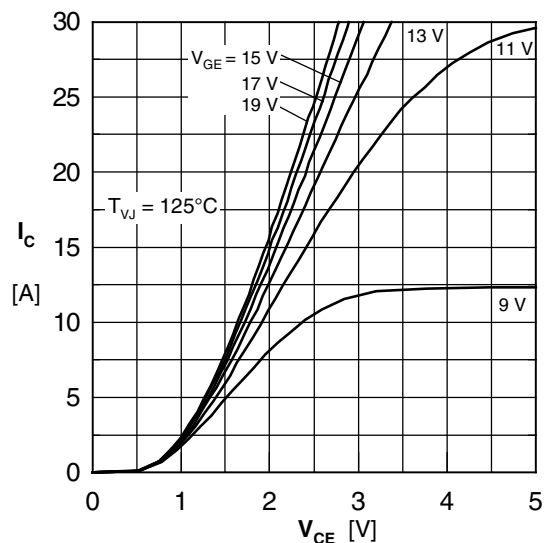


Fig. 2 Typ. output characteristics

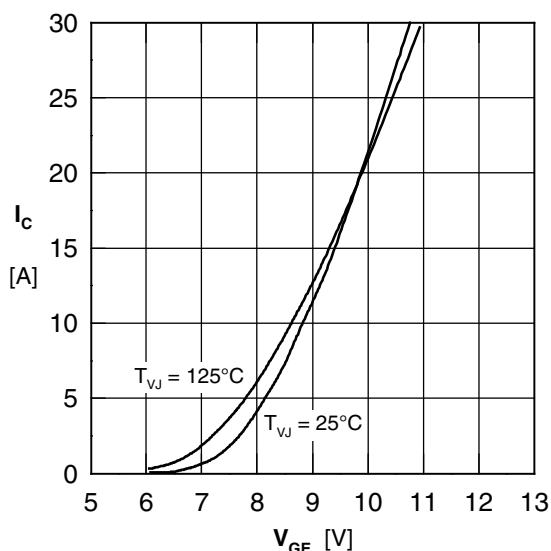


Fig. 3 Typ. transfer characteristics

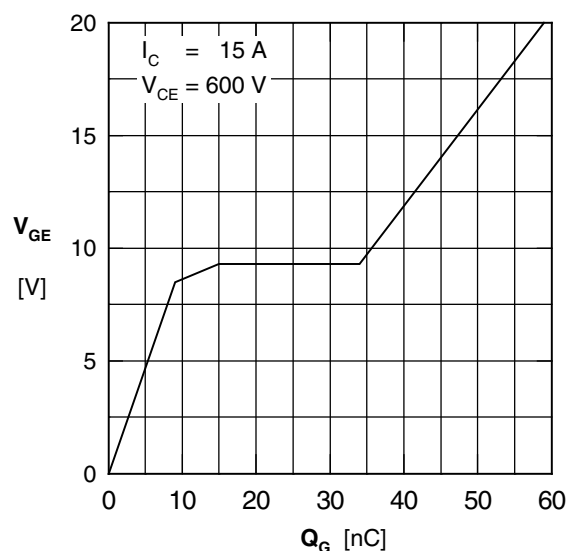


Fig. 4 Typ. turn-on gate charge

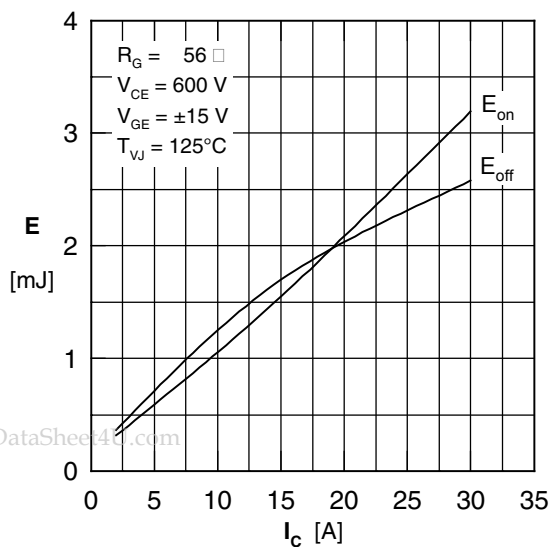


Fig. 5 Typ. switching energy vs. collector current

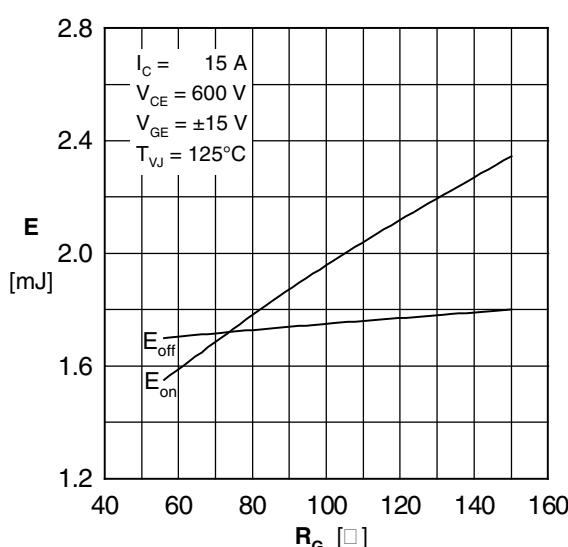


Fig. 6 Typ. switching energy vs. gate resistance